50. (NEW) A process for fabricating a semiconductor device according to claim 38, wherein said process is performed with said filmy die-bonding material comprising one or more resins selected from the group consisting of silicone resin, acrylic resin, polyimide resin and epoxy resin; and

said filmy die-bonding material has a residual volatile component in an amount not more than 3.0% by weight.

C1 Cont.

51. (NEW) A process for fabricating a semiconductor device according to claim 38, wherein said process is performed with said filmy die-bonding material comprising polyimide and epoxy resin comprising one or more resins selected from the group consisting of silicone resin, acrylic resin, polyimide resin and epoxy resin; and

said filmy die-bonding material has a modulus of elasticity of 10 Mpa or less at a temperature of 250°C.

52. (NEW) A process for fabricating a semiconductor device according to claim 38, wherein said process is performed with said filmy die-bonding material comprising polyimide and epoxy resin comprising one or more resins selected from the group consisting of silicone resin, acrylic resin and polyimide resin; resin, polyimide resin and epoxy resin; and

said filmy die-bonding material having, at a stage where the semiconductor chip has been bonded to the support member, a void volume of 10% or less in terms of voids present in the die-bonding material and at an interface between the die-bonding material and the support member.

53. (NEW) A process for fabricating a semiconductor device according to claim 38, wherein said process is performed with said filmy die-bonding material comprising polyimide and epoxy resin comprising one or more resins selected from the group consisting of silicone resin, acrylic resin, polyimide resin and epoxy resin; and

said filmy die-bonding material has a peel strength of 0.5 kgf/5 x 5 mm chip or above at a stage where the semiconductor chip has been bonded to the support member.

C1 Cont.

54. (NEW) A process for fabricating a semiconductor device according to claim 38, wherein said process is performed with said filmy die-bonding material comprising one or more resins selected from the group consisting of silicone resin, acrylic resin, polyimide resin and epoxy resin; and

said filmy die-bonding material i) has a planar dimension not larger than a planar dimension of the semiconductor chip, and ii) not protruding outward from a region of the semiconductor chip at a stage where the semiconductor chip has been bonded to the support member.

55. (NEW) A semiconductor device according to claim 29, wherein said film has a modulus of elasticity of 10 MPa or less at a temperature of 250°C.

56. (NEW) A semiconductor device according to claim 29, wherein said film has a water absorption of 1.5% by volume or less.

57. (NEW) A semiconductor device according to claim 29, wherein said film has a residual volatile component in an amount not more than a 3.0% by weight.

58. (NEW) A semiconductor device according to claim 29, wherein said film has a saturation moisture absorption of 1.0% by volume or less.

Cl' Contd.

59. (NEW) A semiconductor device according to claim 29, wherein said film has, at a stage where the semiconductor chip has been bonded to the support member, a void volume of 10% or less in terms of voids present in the die-bonding material and at an interface between the die-bonding material and the support member.

60. (NEW) A semiconductor device according to claim 29, wherein said film i) has a planar dimension not larger than a planar dimension of the semiconductor chip, and ii) is not protruding outward from a region of the semiconductor chip at a stage where the semiconductor chip has been bonded to the support member.